



DEPOSITION SYSTEMS FOR COMPOUND SEMICONDUCTORS

AIX G5+ C Planetary Reactor[®] for GaN on 150/200 mm Si

AIXTRON

Our technology. Your future.

Single wafer performance with batch reactor benefits

AIX G5+ C Cluster

Increase your productivity and performance

- ▶ Chosen by the best in the industry
- ▶ Highest throughput
- ▶ Lowest Cost of Ownership
- ▶ Highest yield performance
- ▶ 1st fully automated MOCVD platform with Cl_2 in-situ cleaning and cassette-to-cassette wafer handler

AIX G5+ C characteristics

- ▶ Unique axis symmetric wafer performance like Si single wafer reactor
 - Wafer bow
 - Thickness, composition, concentration
 - Device yield
- ▶ Warm ceiling results in lowest heat flux through wafer
 - Smallest wafer bow by vertical temperature gradient
 - Enabling standard Si wafer thickness
- ▶ Customized temperature optimization by recess shaping

Cassette-to-Cassette Wafer Handler



Single Wafer Performance with Batch Reactor Cost Benefit

GaN on Si HEMT thickness uniformity 0.44 % standard deviation without edge exclusion. Mean thickness 3.37 μm .

